

## GSB772SS PNP EPITAXIAL PLANAR TRANSISTOR

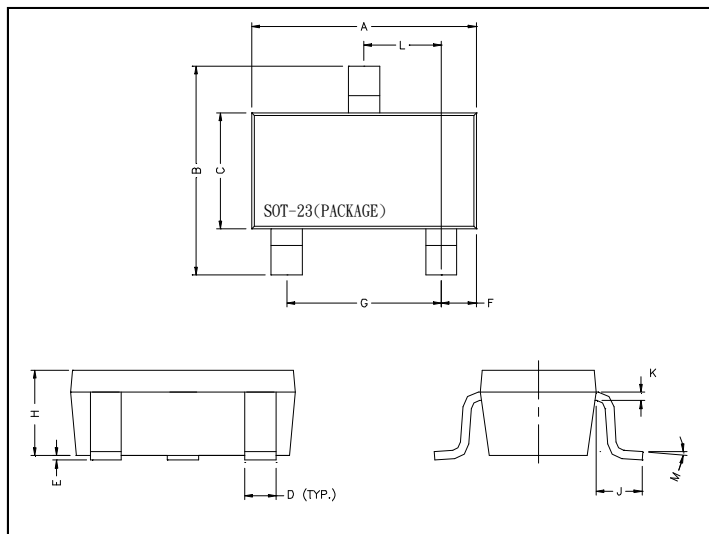
### Description

The GSB772SS is a medium power low voltage transistor, designed for audio power amplifier, DC-DC converter and voltage regulator.

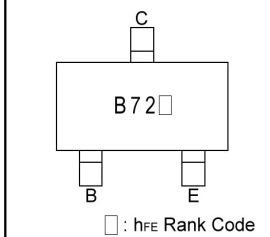
### Features

- High current output up to -3A
- Low saturation voltage

### Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T <sub>J</sub>	+150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 ~ +150	°C
Collector to Base Voltage	V <sub>CB0</sub>	-40	V
Collector to Emitter Voltage	V <sub>CEO</sub>	-30	V
Emitter to Base Voltage	V <sub>EBO</sub>	-5	V
Collect Current(DC)	I <sub>C</sub>	-3	A
Total Power Dissipation	P <sub>D</sub>	750	mW

### Electrical Characteristics(Ta = 25°C)

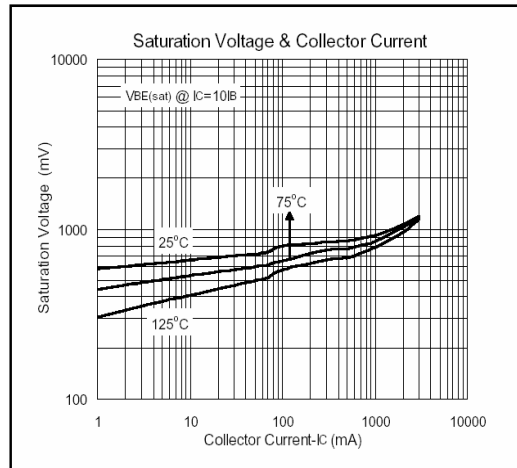
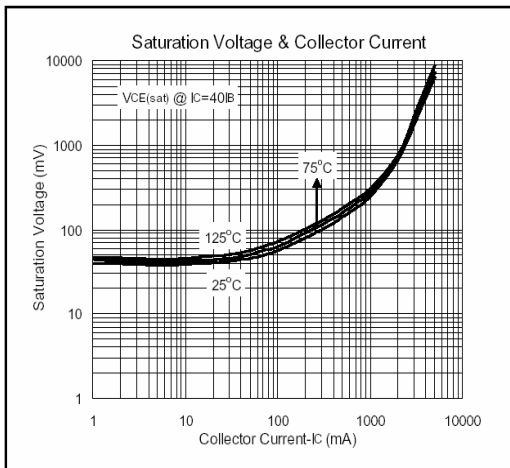
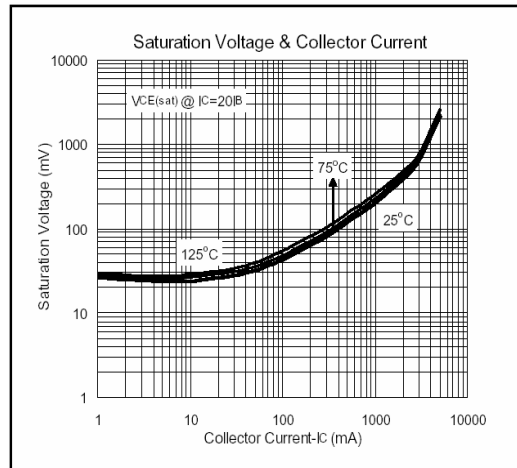
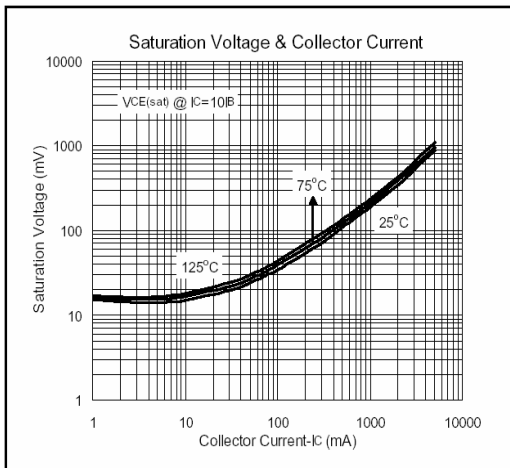
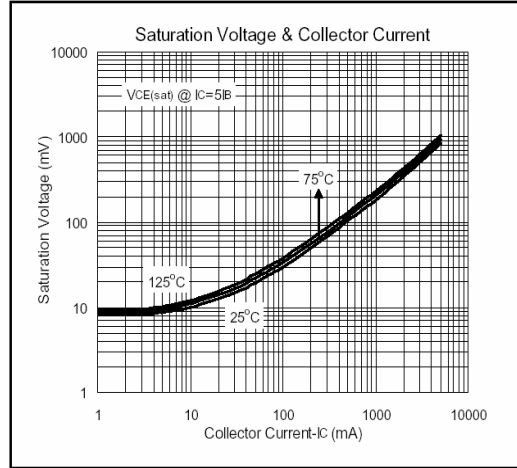
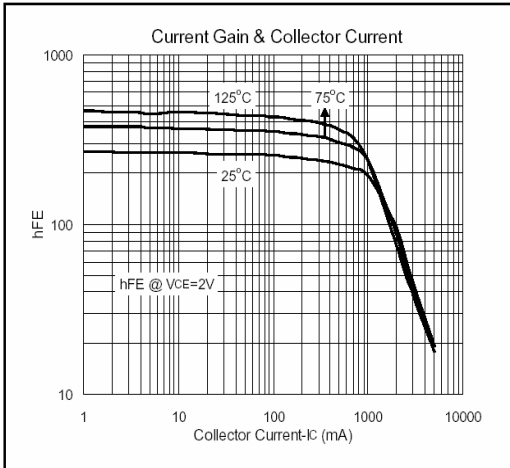
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
V <sub>CB0</sub>	-40	-	-	V	I <sub>C</sub> =-100uA, I <sub>E</sub> =0
V <sub>CEO</sub>	-30	-	-	V	I <sub>C</sub> =-1mA, I <sub>B</sub> =0
V <sub>EBO</sub>	-5	-	-	V	I <sub>E</sub> =-10uA, I <sub>C</sub> =0
I <sub>CB0</sub>	-	-	-1	uA	V <sub>CB</sub> =-30V, I <sub>E</sub> =0
I <sub>EBO</sub>	-	-	-1	uA	V <sub>EB</sub> =-3V, I <sub>C</sub> =0
*V <sub>CE(sat)</sub>	-	-	-0.5	V	I <sub>C</sub> =-2A, I <sub>B</sub> =-200mA
*V <sub>BE(sat)</sub>	-	-1.0	-2.0	V	I <sub>C</sub> =-2A, I <sub>B</sub> =-200mA
*h <sub>FE1</sub>	30	-	-		V <sub>CE</sub> =-2V, I <sub>C</sub> =-20mA
*h <sub>FE2</sub>	100	-	500		V <sub>CE</sub> =-2V, I <sub>C</sub> =-1A
f <sub>T</sub>	-	80	-	MHz	V <sub>CE</sub> =-5V, I <sub>C</sub> =-100mA, f=100MHz
C <sub>ob</sub>	-	55	-	pF	V <sub>CB</sub> =-10V, f=1MHz

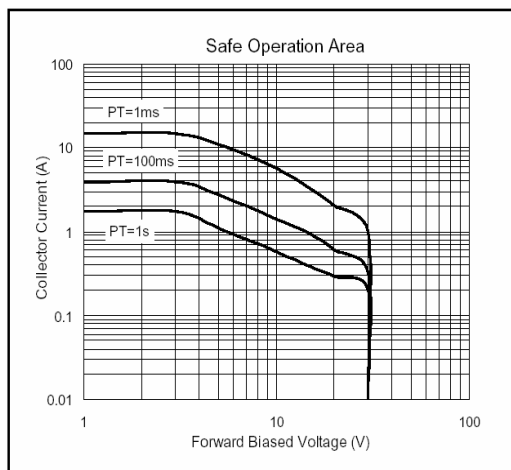
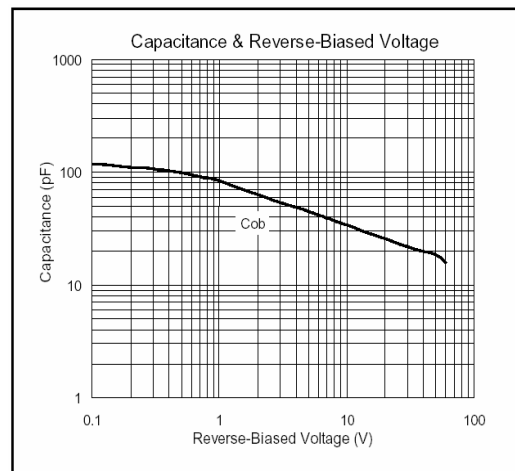
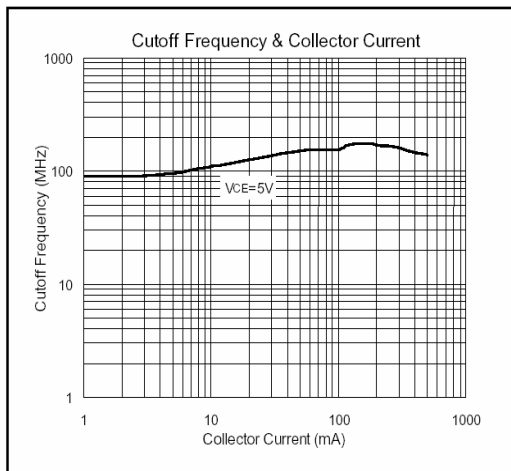
\* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

### Classification Of hFE2

Rank	Q	P	E
Range	100 - 200	160 - 320	200 - 500

## Characteristics Curve





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